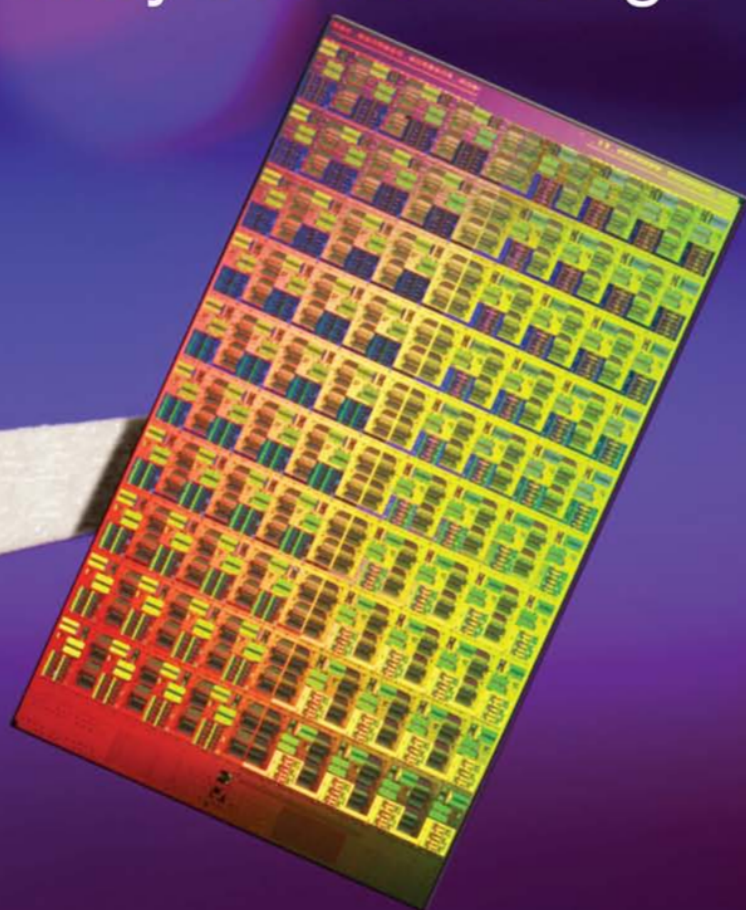


SECOND EDITION

Digital Integrated CIRCUITS

Analysis and Design



John E. Ayers



CRC Press
Taylor & Francis Group

S E C O N D E D I T I O N

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To Kimberly, Jacob, Sarah, and Rachel.

*Their patience and limitless support
made this project possible.*

Contents

Preface.....xv

About the Author xvii

1. Introduction 1

1.1 Historical Perspective and Moore’s Law 1

1.2 Electrical Properties of Digital Integrated Circuits.....8

1.2.1 Logic Function.....9

1.2.2 Static Voltage Transfer Characteristics 14

1.2.3 Transient Characteristics 17

1.2.4 Fan-In and Fan-Out 20

1.2.5 Dissipation 21

1.2.6 Power Delay Product.....25

1.3 Computer-Aided Design and Verification.....25

1.4 Fabrication.....26

1.5 Semiconductors and Junctions.....27

1.6 The MOS Transistor.....28

1.7 MOS Gate Circuits29

1.8 Interconnect30

1.9 Dynamic CMOS31

1.10 Low-Power CMOS.....31

1.11 Bistable Circuits.....32

1.12 Memories.....33

1.13 Input/Output and Interface Circuits.....33

1.14 Practical Perspective34

1.15 Summary34

1.16 Exercises35

References38

2. Fabrication.....39

2.1 Introduction39

2.2 Basic CMOS Fabrication Sequence39

2.3 Advanced Processing for High-Performance CMOS.....44

2.3.1 Copper Metal.....45

2.3.2 Metal Gates48

2.3.3 High-κ Gate Dielectric49

2.4 Lithography and Masks50

2.5 Layout and Design Rules53

2.5.1 Minimum Line Widths and Spacings55

2.5.2 Contacts and Vias57

2.6	Testing and Yield.....	57
2.7	Packaging	61
2.8	Burn-In and Accelerated Testing	63
2.9	Practical Perspective	63
2.10	Summary	63
2.11	Exercises	64
	References	64
3.	Semiconductors and p-n Junctions	67
3.1	Introduction	67
3.2	Crystal Structure of Silicon	67
3.3	Energy Bands.....	67
3.4	Carrier Concentrations.....	69
3.4.1	Intrinsic Silicon	70
3.4.2	n-Type Silicon	70
3.4.3	p-Type Silicon	72
3.5	Current Transport	72
3.6	Carrier Continuity Equations.....	75
3.7	Poisson's Equation.....	75
3.8	The p-n Junction.....	76
3.8.1	Zero Bias (Thermal Equilibrium)	77
3.8.1.1	Built-In Voltage V_{bi}	79
3.8.1.2	Depletion Width W	79
3.8.2	Depletion Capacitance	80
3.8.3	Forward Bias Current.....	83
3.8.3.1	Short-Base n^+ -p Junction.....	85
3.8.3.2	Long-Base n^+ -p Junction	87
3.8.4	Reverse Bias	87
3.8.5	Reverse Breakdown	88
3.9	Metal-Semiconductor Junctions.....	88
3.10	SPICE Models	90
3.11	Practical Perspective	91
3.12	Summary	91
3.13	Exercises	92
	References	93
4.	The MOS Transistor.....	95
4.1	Introduction	95
4.2	The MOS Capacitor.....	97
4.3	Threshold Voltage	100
4.4	MOSFET Current-Voltage Characteristics	105
4.4.1	Linear Operation.....	106
4.4.2	Saturation Operation.....	110
4.4.3	Subthreshold Operation.....	110
4.4.4	Transit Time	114

- 4.5 Short-Channel MOSFETs 115
 - 4.5.1 The Short-Channel Effect 115
 - 4.5.2 Narrow-Channel Effect..... 116
 - 4.5.3 Drain-Induced Barrier Lowering..... 117
 - 4.5.4 Channel Length Modulation..... 118
 - 4.5.5 Field-Dependent Mobility and Velocity Saturation 119
 - 4.5.6 Transit Time in Short-Channel MOSFETs 125
- 4.6 MOSFET Design 126
- 4.7 MOSFET Capacitances 133
 - 4.7.1 Oxide Capacitances 134
 - 4.7.2 p-n Junction Capacitances 136
 - 4.7.3 The Miller Effect 140
- 4.8 MOSFET Constant-Field Scaling..... 141
- 4.9 SPICE MOSFET Models 142
 - 4.9.1 MOSFET Level 1 Model 144
 - 4.9.2 Berkeley Short-Channel Insulated Gate Field Effect Transistor Model 146
 - 4.9.2.1 BSIM1 Parameters 147
 - 4.9.2.2 BSIM1 Threshold Voltage 148
 - 4.9.2.3 BSIM1 Drain Current-Linear Region..... 149
 - 4.9.2.4 BSIM1 Drain Current-Saturation Region 150
 - 4.9.2.5 BSIM1 Drain Current-Subthreshold Region 150
 - 4.9.2.6 Hand Calculations Related to the BSIM1 150
- 4.10 SPICE Demonstrations 151
- 4.11 Practical Perspective 156
- 4.12 Summary 156
- 4.13 Exercises 158
- References 160
- 5. MOS Gate Circuits 163**
 - 5.1 Inverter Static Characteristics 163
 - 5.2 Critical Voltages..... 167
 - 5.2.1 Output High-Voltage V_{OH} 168
 - 5.2.2 Output Low-Voltage V_{OL} 168
 - 5.2.3 Input Low-Voltage V_{IL} 169
 - 5.2.4 Input High-Voltage V_{IH} 170
 - 5.2.5 Switching Threshold (Midpoint) Voltage V_M 171
 - 5.2 Dissipation 175
 - 5.4 Propagation Delays..... 179
 - 5.5 Fan-Out..... 182
 - 5.6 NOR Circuits 185
 - 5.7 NAND Circuits..... 186
 - 5.8 Exclusive OR (XOR) Circuit 187
 - 5.9 General Logic Design 188